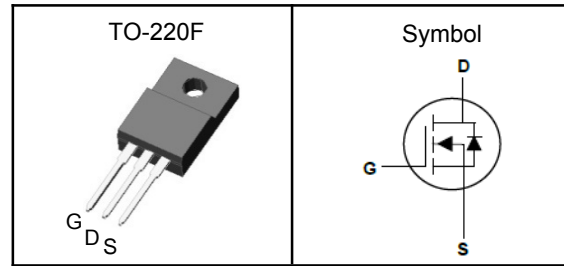


N-Channel Enhancement Mode MOSFET
Features

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant
- 100% UIS and Rg Tested

Pin Description

Applications

- High Efficiency Switch Mode Power Supplies
- Electronic Lamp Ballasts
- UPS

V_{DSS}	700	V
$R_{DS(ON)-Typ}$	790	m Ω
I_D	12	A

Absolute Maximum Ratings($T_J=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit
V_{DSS}	Drain-Source Voltage	700	V
V_{GSS}	Gate-Source Voltage	± 30	V
T_J	Maximum Junction Temperature	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
E_{AS}	Single Pulse Avalanche Energy ^③	580	mJ
$I_{DM}^{①}$	Pulse Drain Current Tested	48	A
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ^①	62.5	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ^①	4.2	$^\circ\text{C}/\text{W}$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150 $^\circ\text{C}$.

Note ③ : Surface Mounted on 1in² FR-4 board with 1oz.



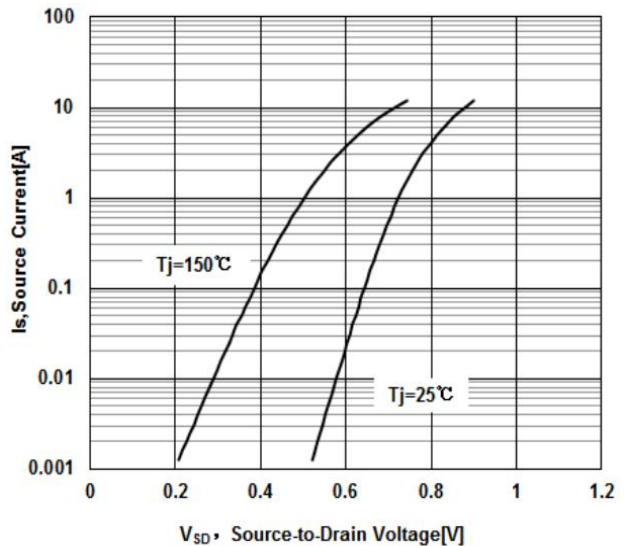
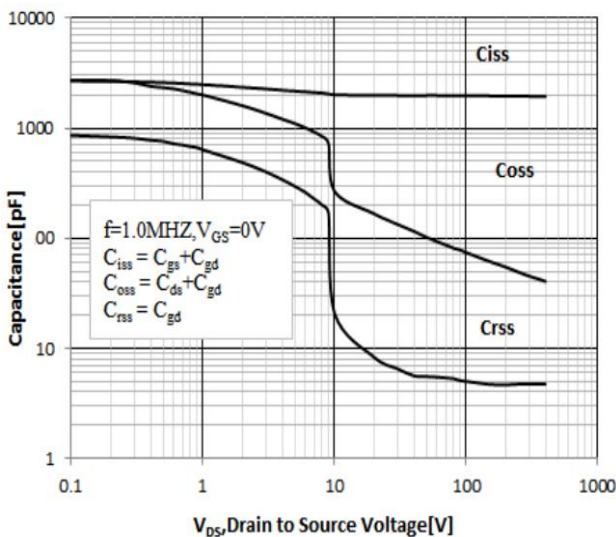
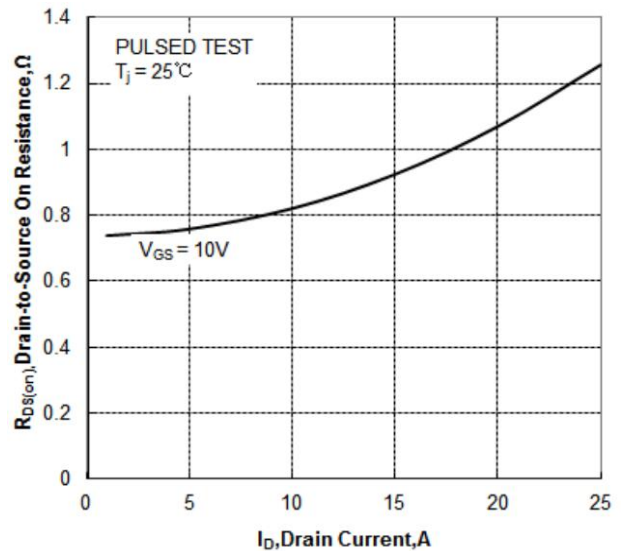
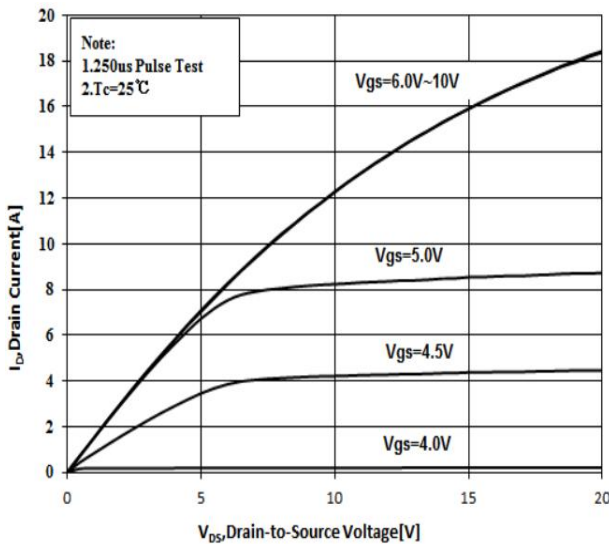
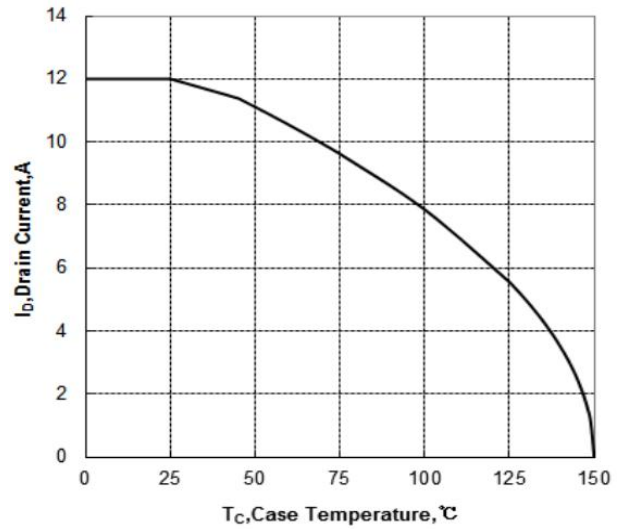
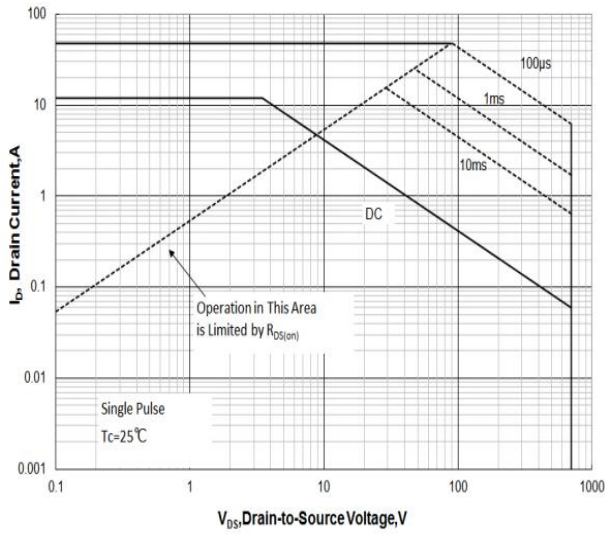
N-Channel Enhancement Mode MOSFET

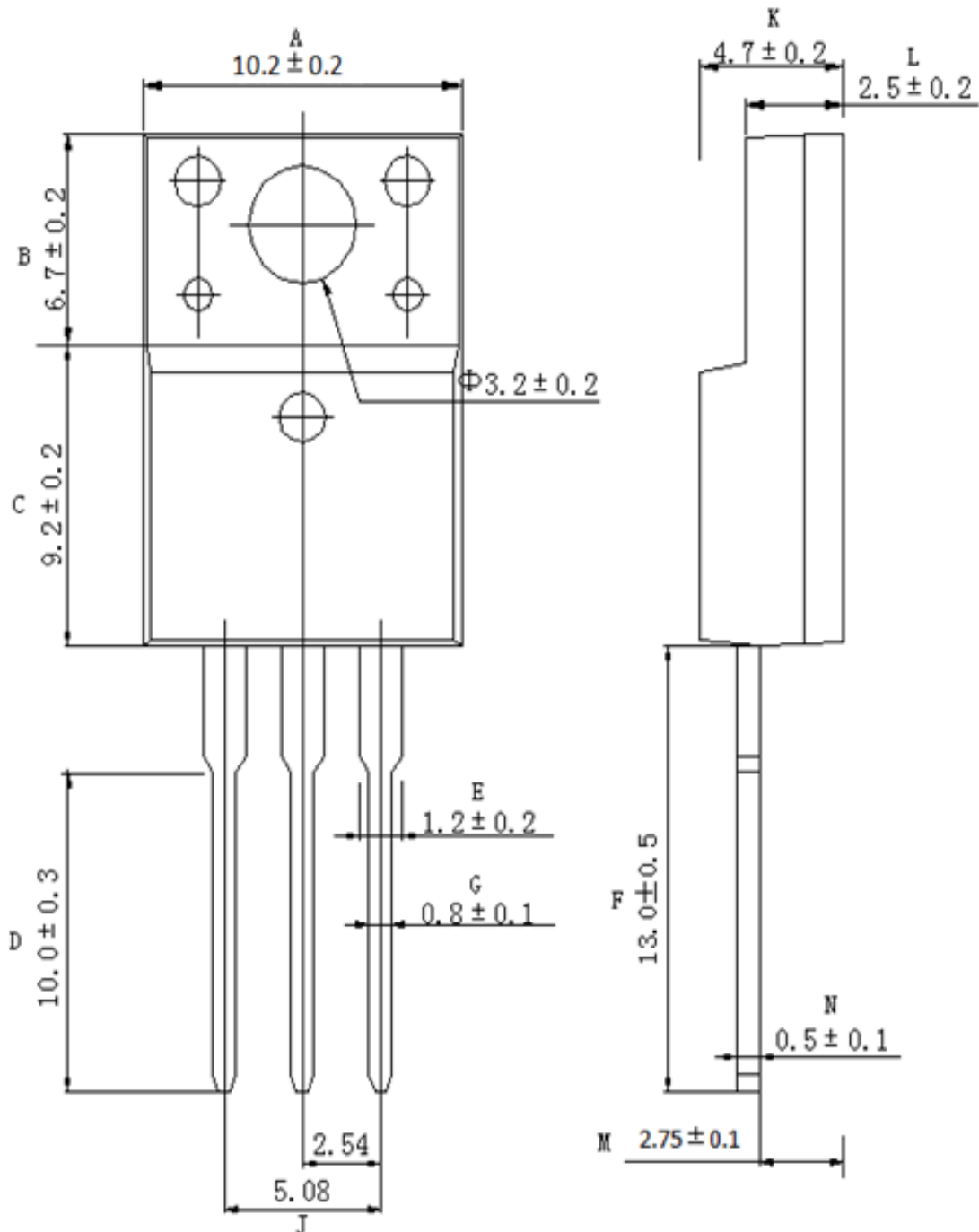
Electrical Characteristics ($T_J=25^{\circ}\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	700	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=700V, V_{GS}=0V$	---	---	1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	---	4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 30V, V_{DS}=0V$	---	---	± 100	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=6A$	---	790	950	$m\Omega$
g_{fs}	Forward Transconductance	$V_{DS}=15V, I_D=6A$	---	12	---	S
Dynamic Characteristics ^⑤						
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=25V,$ Freq.=1MHz	---	1981	---	pF
C_{oss}	Output Capacitance		---	147	---	
C_{riss}	Reverse Transfer Capacitance		---	7	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=350V, R_G=10\Omega,$ $I_D=12A$	---	28	---	nS
T_r	Turn-on Rise Time		---	26	---	
$T_{d(off)}$	Turn-off Delay Time		---	64	---	
T_f	Turn-off Fall Time		---	45	---	
Q_g	Total Gate Charge	$V_{DD}=560V,$ $V_{GS}=10V, I_D=12A$	---	39	---	nC
Q_{gs}	Gate-Source Charge		---	9.2	---	
Q_{gd}	Gate-Drain Charge		---	16	---	
Source-Drain Characteristics ($T_J=25^{\circ}\text{C}$)						
$V_{SD}^{\text{④}}$	Diode Forward Voltage _z	$V_{GS}=0V, I_S=12A, T_J=25^{\circ}\text{C}$	---	---	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=12A,$ $di/dt=100A/\mu s, T_J=25^{\circ}\text{C}$	---	536	---	nS
Q_{rr}	Reverse Recovery Charge		---	4.7	---	nC

Note ④ : Pulse test (pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$).

Note ⑤ : Guaranteed by design, not subject to production testing.

N-Channel Enhancement Mode MOSFET
Typical Characteristics


N-Channel Enhancement Mode MOSFET
TO-220F Package Outline Data




印字说明

印字说明

FS12N70YF

AABBCC

第一行标记为物料型号代码

第二行为AA为内部识别码，BB为表示年份，例如22即表示2022年，CC表示周期，例如01即表示第一周；2201即表示2022年第一周生产。